

Attorney Docket #10010872-1

**Amendments to the Claims**

This list of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-11 (Canceled)

12. (currently amended) A ~~semiconductor device sloped via contact on a wafer having front and back sides~~, comprising:

a wafer of resistive semiconductor material, having a through hole, a front side, and a back side, wherein the width of the hole increases from a minimum width on one side to a maximum width on the other side;

a front contact on the front side of the wafer;

a back contact on the back side of the wafer; and

a metal layer that adheres to the inner walls of the through hole and connects the front contact to the back contact. ~~a via through the wafer connecting the front contact to the back contact.~~, wherein

~~the via walls have a metal coating, and~~

~~the via increases in width.~~

13. (currently amended) The ~~sloped via contact~~ semiconductor device as in claim 12, wherein the ~~via through hole~~ is less than 80 microns at its widest.

14. (currently amended) The ~~sloped via contact~~ semiconductor device as in claim 13, wherein the ~~via through hole~~ is less than 50 microns at its widest.

15. (currently amended) The ~~sloped via contact~~ semiconductor device as in claim 13 wherein the metal ~~coating layer~~ on the ~~via through hole~~ is at least 1000 Angstroms thick where the ~~via through hole~~ is the narrowest.

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16. (currently amended) The ~~sloped-via-contact~~ semiconductor device as in claim 15, wherein the metal ~~coating~~ layer is selected from the group consisting of NiChrome and gold.

17. (currently amended) The ~~sloped-via-contact~~ semiconductor device as in claim 15, wherein the metal ~~coating~~ layer on the ~~via~~ through hole is partially plated.

18-20. (canceled)

21. (currently amended) The ~~sloped-via-contact~~ semiconductor device as in claim 13, wherein the slope of the ~~via~~ walls of the through hole is not constant.

22. (currently amended) The ~~sloped-via-contact~~ semiconductor device as in claim 13, wherein the ~~via~~ walls of the through hole are curved.